Constant Voltage / Constant Current Secondary-Side Controller

Description

The NCS1002A is a performance upgrade from the NCS1002 focused on reducing power consumption in applications that require more efficient operation. It is a highly integrated solution for Switching Mode Power Supply (SMPS) applications requiring a dual control loop to perform Constant Voltage (CV) and Constant Current (CC) regulation. The NCS1002A integrates a 2.5 V voltage reference and two precision op amps. The voltage reference, along with Op Amp 1, is the core of the voltage control-loop. Op Amp 2 is an independent, uncommitted amplifier specifically designed for the current control. Key external components needed to complete the two control loops are: (a) A resistor divider that senses the output of the power supply (battery charger) and fixes the voltage regulation set point at the specified value. (b) A sense resistor that feeds the current sensing circuit with a voltage proportional to the DC output current. This resistor determines the current regulation set point and must be adequately rated in terms of power dissipation. The NCS1002A comes in a small 8-pin SOIC package and is ideal for space-shrunk applications such as battery chargers.

Features

- Low Input Offset Voltage: 0.5 mV, Typ
- Input Common-Mode Range includes Ground
- Low Quiescent Current: 75 μ A per Op Amp at V_{CC} = 5 V
- Large Output Voltage Swing
- Wide Power Supply Range: 3 V to 36 V
- High ESD Protection: 2 kV
- This is a Pb–Free Device

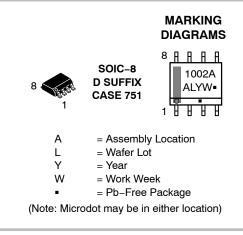
Typical Applications

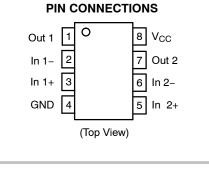
- Battery Chargers
- Switch Mode Power Supplies

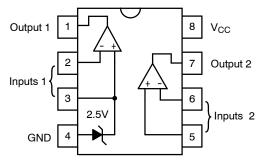


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ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

MAXIMUM RATINGS

Parameter	Symbol	Rating	Unit
Supply Voltage (V _{CC} to GND) (Operating Range V _{CC} = 3 V to 36 V)	V _{CC}	36	V
Differential Input Voltage	V _{id}	36	V
Input Voltage	Vi	-0.3 to +36	V
ESD Protection Voltage at Pin Human Body Model	V _{ESD}	2000	V
Maximum Junction Temperature	TJ	150	°C
Specification Temperature Range (T _{min} to T _{max})	T _A	-40 to +105	°C
Operating Free-Air Temperature Range	T _{oper}	–55 to +125	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Parameter		Symbol	Rating	Unit
Thermal Resistance	Junction-to-Ambient	R_{\thetaJA}	175	°C/W

ELECTRICAL CHARACTERISTICS

Symbol	Characteristics	Conditions	Min	Тур	Max	Unit
I _{CC}	Total Supply Current, excluding current in the Voltag load; -40 \leq T_A \leq +105°C	ge Reference V _{CC} = 5 V, no		0.15	0.25	mA
Icc	Total Supply Current, excluding Current in the Voltage Reference V_{CC} = 30 V, no load; –40 \leq T_A \leq +105°C			0.2	0.3	mA

OP AMP 1 (OP AMP WITH NONINVERTING INPUT CONNECTED TO THE INTERNAL v_{ref} (V $_{CC}$ = 5 V, T $_{A}$ = 25°C unless otherwise noted)

V _{IO}	Input Offset Voltage	$T_A = 25^{\circ}C$			2.0	mV
		$-40 \le T_A \le +105^{\circ}C$			3.0	mV
DVIO	Input Offset Voltage Drift (-40 $\leq T_A \leq +105^{\circ}C$)			7.0		μV/°C
I _{IB}	Input Bias Current (Inverting Input Only)			20	150	nA
AVD	Large Signal Voltage Gain (V _{CC} = 15 V, R _L = 2 k Ω , V _{ICM} = 0 V)			100		V/mV
PSRR	Power Supply Rejection (V _{CC} = 5.0 V to 30 V, V _{OUT}	· = 2 V)	80	100		dB
I _{SOURCE}	Output Source Current (V _{CC} = 15 V, V _{OUT} = 2.0 V, V_{id} = 1 V)		20	40		mA
Ι _Ο	Short Circuit to GND (V _{CC} = 15 V)			40	60	mA
I _{SINK}	Output Current Sink (V _{id} = -1 V)	V _{CC} = +15 V, V _{OUT} = 0.2 V (Note 1)	1	10		mA
		V_{CC} = +15 V, V_{OUT} = 2 V	10	20		mA
V _{OH}	Output Voltage Swing, High (V _{CC} = 30 V)	$R_L = 2 k\Omega, T_A = 25^{\circ}C$	26	27		V
		$-40 \le T_A \le +105^{\circ}C$	26			
		$R_L = 10 \text{ k}\Omega, T_A = 25^{\circ}C$	27	28		
		$-40 \le T_A \le +105^{\circ}C$	27			
V _{OL}	Output Voltage Swing, Low	$R_L = 10 \text{ k}\Omega, T_A = 25^{\circ}C$		5.0	50	mV
SR	Slew Rate (AV = +1, V _i = 0.5 V to 2 V, V _{CC} = 15 V, R _L = 2 k\Omega, C _L = 100 pF)		0.2	0.4		V/μs
GBP	Gain Bandwidth Product (V _{CC} = 30 V, AV = +1, (Note 1) R _L = 2 k Ω , C _L = 100 pF, f = 100 kHz, V _{IN} = 10 mV _{PP})		0.5	0.9		MHz
THD	Total Harmonic Distortion (f = 1 kHz, AV = 10, R _L = 2 k Ω , V _{CC} = 30 V, V _{OUT} = 2 V _{PP})			0.08		%

OP AMP 2 (INDEPENDENT OP AMP) (V_{CC} = 5.0 V, T_A = 25^{\circ}C unless otherwise noted)

V _{IO}	Input Offset Voltage	T _A = 25°C		0.5	2.0	mV
		$-40 \le T_A \le +105^{\circ}C$			3.0	
DV _{IO}	Input Offset Voltage Drift (-40 $\leq T_A \leq +105^{\circ}C$)			7.0		μV/°C
I _{IO}	Input Offset Current	$T_A = 25^{\circ}C$		2.0	75	nA
		$-40 \le T_A \le +105^{\circ}C$			150	
Ι _Β	Input Bias Current	$T_A = 25^{\circ}C$		20	150	nA
		$-40 \le T_A \le +105^{\circ}C$			200	
AVD	Large Signal Voltage Gain ($V_{CC} = 15$ V,	$T_A = 25^{\circ}C$	50	100		V/mV
	$R_L = 2 k\Omega, V_{OUT} = 1.4 V \text{ to } 11.4 V$	$-40 \le T_A \le +105^{\circ}C$	25			
PSRR	Power Supply Rejection (V_{CC} = 5 V to 30 V)		80	100		dB

1. Guaranteed by design and/or characterization.

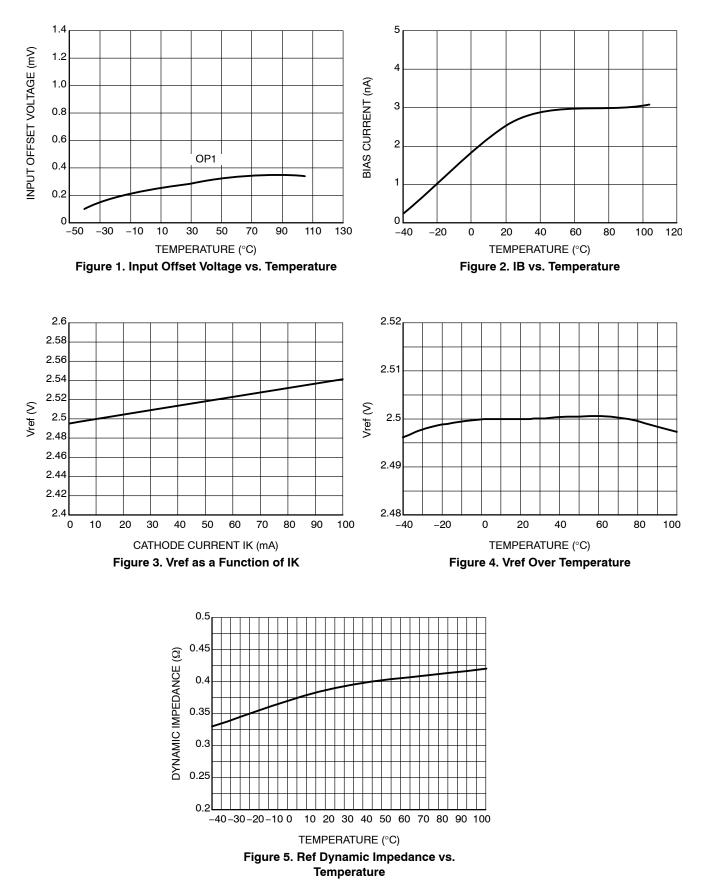
ELECTRICAL CHARACTERISTICS (continued)

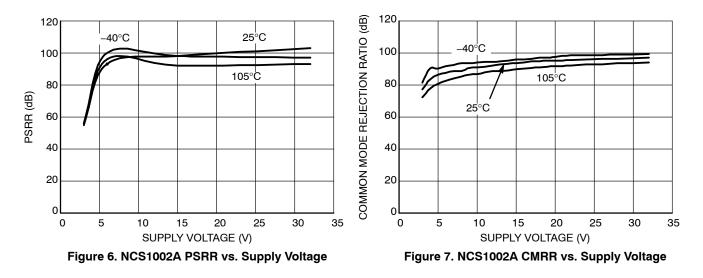
Symbol	Characteristics	Conditions	Min	Тур	Max	Unit	
OP AMP 2 (INDEPENDENT OP AMP) (continued) ($V_{CC} = 5.0 \text{ V}$, $T_A = 25^{\circ}C$ unless otherwise noted)							
V _{ICM}	Input Common Mode Voltage Range (Note 2) $(V_{CC} = +30 \text{ V})$	T _A = 25°C	0		V _{CC} – 1.5	V	
		$-40 \le T_A \le +105^{\circ}C$	0		V _{CC} - 2.0		
CMRR	Common Mode Rejection Ratio (Note 4)	0 to V _{CC} – 1.7 V, T _A = 25°C	70	85		dB	
		$0 \text{ to } V_{CC} - 2.2 \text{ V} \\ -40 \le T_A \le +105^{\circ}\text{C}$	60				
ISOURCE	Output Current Source (V _{CC} = 15 V, V _{OUT} = 2 V, V	_{ID} = +1 V)	20	40		mA	
Ι _Ο	Short-Circuit to GND (V _{CC} = 15 V)			40	60	mA	
I _{SINK}	Output Current Sink (V _{ID} = -1 V)	V_{CC} = +15 V, V_{OUT} = 0.2 V	1	10		mA	
		V _{CC} = +15 V, V _{OUT} = 2 V	10	20		mA	
V _{OH}	Output Voltage Swing, High (V_{CC} = 30 V)	$R_L = 2 \text{ k}\Omega, T_A = 25^{\circ}C$	26	27		V	
		$-40 \le T_A \le +105^{\circ}C$	26				
		R_L = 10 kΩ, T_A = 25°C	27	28			
		$-40 \le T_A \le +105^{\circ}C$	27				
V _{OL}	Output Voltage Swing, Low	R_L = 10 kΩ, T_A = 25°C		5.0	50	mV	
SR	Slew Rate (AV = +1, V_i = 0.5 V to 3 V, V_{CC} = 15 V,	R _L = 2 kΩ, C _L = 100 pF)	0.2	0.4		V/μs	
GBP	Gain Bandwidth Product (V _{CC} = 30 V, AV = +1, R _L = 2 k Ω , C _L = 100 pF, f = 100 kHz, V _{IN} = 10 mV _{PP}) (Note 4)		0.5	0.9		MHz	
THD	Total Harmonic Distortion (f = 1 kHz, AV = 10, R _L = 2 k Ω , V _{CC} = 30 V, V _{OUT} = 2 V _{PP})			0.08		%	
e _{noise}	Equivalent Input Noise Voltage (f = 1 kHz, R _S = 10	0 Ω, V _{CC} = 30 V)		50		nV/√ Hz	

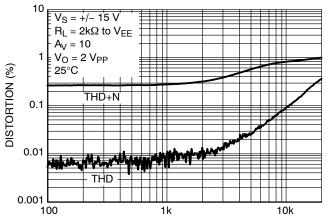
VOLTAGE REFERENCE (V_{CC} = 5.0 V, T_A = 25°C unless otherwise noted)

۱ _K	Cathode Current		0.05		100	mA
V _{ref}	Reference Voltage (I _K = 1 mA)	$T_A = 25^{\circ}C$	2.49	2.5	2.51	V
		$-40 \le T_A \le +105^{\circ}C$	2.48	2.5	2.52	
ΔV_{ref}	Reference Deviation over Temperature (V_{KA} = V_{ref}, I_K = 10 mA, –40 \leq T_A \leq +105°C) (Note 4)			7.0	30	mV
I _{min}	Minimum Cathode Current for Regulation (2.4875 $V_f \leq V_{KA} \leq 2.5125 \; V_f)$			10	50	μA
I ZKA I	Dynamic Impedance (Note 3) (V _{KA} = V _{ref} , I _K = 1 mA to 100 mA, f < 1 kHz)			0.2	0.5	Ω

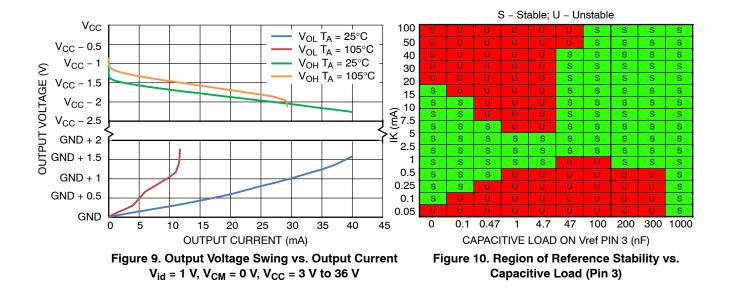
The input common-mode voltage of either input signal should not be allowed to go negative by more than 0.3 V. The upper end of the common-mode range is V_{CC} - 1.5 V. Both inputs can go to V_{CC} + 0.3 V without damage.
The Dynamic Impedance is defined as I ZKA I = ΔV_{KA} / ΔI_K.
Guaranteed by design and/or characterization.







FREQUENCY (Hz) Figure 8. Distortion vs. Frequency



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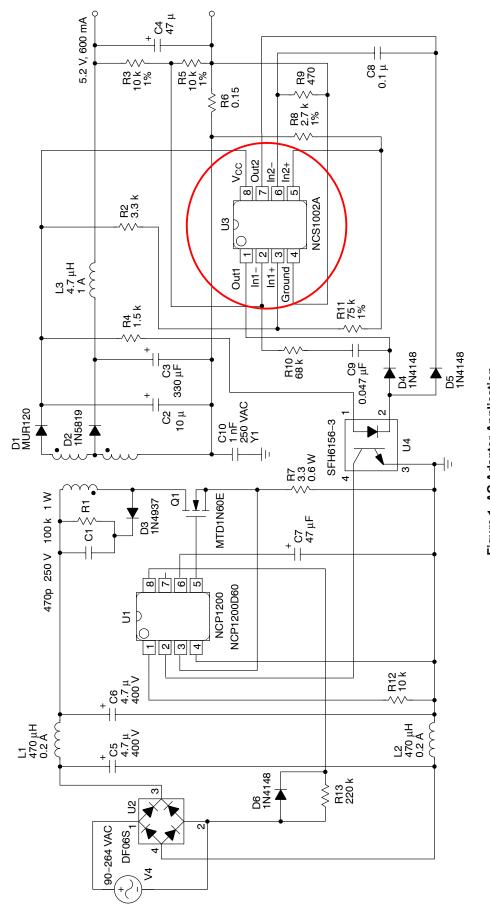


Figure 1. AC Adapter Application

ORDERING INFORMATION

Device	Package	Shipping [†]
NCS1002ADR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOIC-8 NB CASE 751-07 ISSUE AK

NOTES:

2

3

4

5.

6

PER SIDE.

DIM

Α

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С

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Μ

N S

STANDARD IS 751-07.

4.80

3.80

1.35

0.33

0.10

0.19

0.40

0.25

5.80

0

1.27

MIN MAX

5.00

BSC

1. DIMENSIONING AND TOLERANCING PER

ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.

MAXIMUM MOLD PROTRUSION 0.15 (0.006)

DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR

PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION. 751-01 THRU 751-06 ARE OBSOLETE. NEW

INCHES

MIN MAX

0.050 BSC

0.197

0.157

0.069

0.010

8

0.189

0.51 0.013 0.020

0.25 0.004 0.010

1.27 0.016 0.050

0

0.50 0.010 0.020

6.20 0.228 0.244

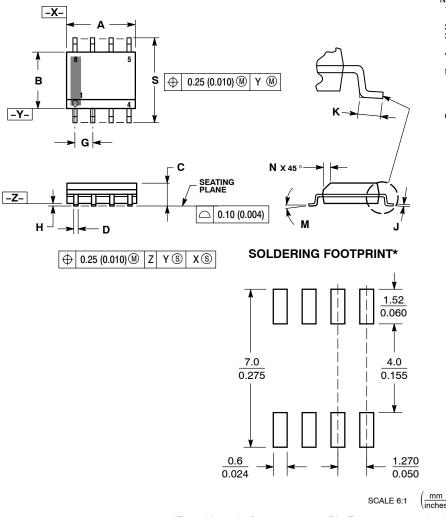
4.00 0.150

1.75 0.053

0.25 0.007

8 °

DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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